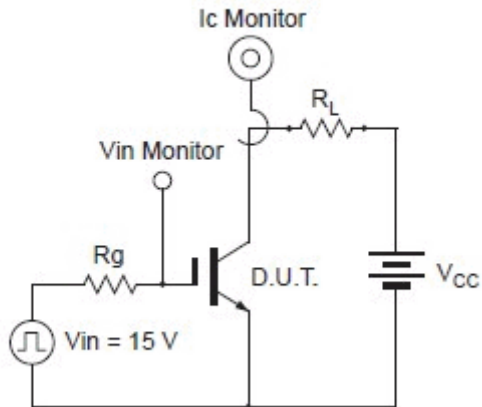


Diagrams



RJH3044 absolute maximum ratings:

- (1) Collector to emitter voltage V_{CES} : 360 V
- (2) Gate to emitter voltage V_{GES} : ± 30 V
- (3) Collector current I_C : 30 A
- (4) Collector peak current $i_{c(peak)}$: 200 A
- (5) Collector to emitter diode Forward peak current $i_{DF(peak)}$: 100 A
- (6) Collector dissipation P_C : 20 W
- (7) Junction to case thermal impedance θ_{j-c} : 6.25 $^{\circ}C/W$
- (8) Junction temperature T_j : 150 $^{\circ}C$
- (9) Storage temperature T_{stg} : -55 to +150 $^{\circ}C$

RJH3044 features:

- (1) Trench gate and thin wafer technology (G6H-II series)
- (2) High speed switching: $t_r = 80$ ns typ., $t_f = 150$ ns typ.
- (3) Low collector to emitter saturation voltage: $V_{CE(sat)} = 1.5$ V typ.
- (4) Low leak current: $I_{CES} = 1$ mA max.
- (5) Built-in Fast Recovery Diode: $V_F = 1.4$ V typ., $t_{rr} = 23$ ns typ
- (6) Isolated package: TO-220FL.